EtA?JNS IN *CcCr* INVE5TIGATED By NiWI'WA DEWLARIZATION.

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Abstract. Polarized neutrons ($\lambda = 0.47$ nm) are transmitted through \mathbb{R}^p and magnetron sputtered CoCr films (0.3-5 μ m thick) wth the polarization vectdr in the plane or perpendicular to the plane of the film. In the former case we can deduce from the deplarization the effective height heff of the darains fran the angular **aependence** of the depolarization the $\text{section width } \delta$ (which is proportional to the **domain** width) in the remanent states after perpendicular and after in-plane saturation.

As expected, h&f appears to **be larger** after perpendicular saturaticn and for afilm thickness h **400 nm,** hff **approaches** h. **This** is attributed to the disappearance of reversed spike domains in the thinnest films. The lower heff found in magnetron films with a lower surface/bulk coercivity ratio is also consistent with spike domain theory. The section width $\hat{\theta}$ is found to be proportional to hx with x depending *cn* the preparation or magnetic history of **the** film between **0.6** and \varnothing .8. For magnetron films δ is \sim 1.5 as large as in RF films of **equal** thickness, in qualitative agreemmt **ody** with the fact that **K1** is twice as large as for **RF** films.

INTRODUCTTON.

For CoCr sputtered films with their typical columnar morphology discussion remains about the particle vs continuous magnetic behaviour. It is well known that the morphology and crystal structure and therefore the magnetic properties of these films depend strongly on the deposition anditions **[l].** In order to understand the magnetization process, domain studies are of great importance. For such studies Neutron Depolarization (ND) is a unique method, especially in studying the bulk of thick films (> **5pKd** nm), axpl-tary to Iarentz **Microsccgy** which can *cdy* **be** applied to thin films (< **2EU** nm) . Most *other* techniques are ccnfined to the surface.

men a polarized neutron beam **passes** through a ferramgnetic **specimen,** the polarization vector precesses around the magnetic indudicn due to the magnetization **Ms** in the magnetic &amins. In **ND** the polarization vector is adjusted **by mans** of a "polarization turner" along one of the (x,y,z) directions of the Iakoratory **system.** *Ety* means of a **second** plarization turner after transmission the component of the polarization vector

- as it emerges out of the sample - along any one of these directims *can* **be** analysed. Thus, a **(3x3)** deplarization matrix *can* **be measured [2].** In this paper **we** only consider the

Fig. 1 Schematic view of the neutron transmission experiment.

diagonal elements D_{XX} , D_{YY} , D_{ZZ} .

Let us illustrate the relevance of ND with the model of Fig. 1 in **which** the dcmains extend throqh the **thickness** or "height" h *cb* the film, defining (x,y,z) as indicated.

In perpendicular transmission the precession angle is + or $-\phi_{m}$, with

$$
\phi_{m} = 5.72 \times 10^{8} (M_{s} h). \lambda \tag{1}
$$

where M_S is in A/m and the neutron wavelength λ and h are in mer. In non-perpendicular transmission, neutron trajectories passing a domain boundary occur, so the precession angle along them is smaller than ϕ_m , hence $\cos \phi$ and also $\cos \phi$ is closer to 1. In an earlier analogous study [3] on thick electrodeposited Ni films we stated that $D_{ZZ} = \langle \cos \phi \rangle$ for all transmission angles θ . In case of domains of equal width **he** can deduce from [3], eq. (14) the following linear relationship between $\cos \phi$ and $|\theta|$:

 $D_{ZZ} = \cos \phi$ = $\cos \phi_m + \theta | f(\phi_m)$, $(\emptyset \& \theta \& \arctan(\delta/h))$

with

$$
f(\phi_m) = \frac{h}{\delta} \frac{\sin \phi_m}{\phi_m} - \cos \phi_m \qquad (2)
$$

Fran *eq.* (1) and **(2)** we obtain the follcwing information: D_{ZZ} ($\theta = \emptyset$) yields the height of the domains and the quantity $f(\phi_m)$; then, from the slopes of the measured D_{ZZ} for small $\mid \theta \mid$ we can determine δ .

When the domains have unequal widths, it is obvious that *eq.* **(2)** remins valid in *good* approximately provided I **6** I is *so* small that contributions due to neutron trajectories passing $2, 3, \ldots$ domain walls are negligible. Then the quantity δ is defined by the formula $1/\delta = \langle 1/\delta_1 \rangle$, with δ_1 the domain section width as indicated in Fig. 1.

We realize that because of the "spaghetti" or "chain of column" like domain structure $[4,5]$, the quantity δ may be larger than the actual domain width. We will refer to δ as "domain section width". This paper deals mainly with the quantities δ and heff for **RF** and magnetron sputtered **Cdr** films in the rment states after perpendicular **and after** in-plane saturation.

EXPERIMENTAL.

The samples were sputtered from alloyed Co81Cr19 targets of **4"** and **3"** diamter respectively, on **Si(l00)** substrates in a Leytnld Hereaus RF-sputter apparatus **(2400)** either without *(so* called 'mfihs') or with magnetron facilities *(so* called 'magnetron films'). Films were sputtered in batches of **16 (RF)** *cr* **23** (magnetron) on substrates with dirnensions **10x10** m2. Each film was characterized by a VSM measurement yielding the wlwe aOerCiVitY *Hcv* and the prcduct **MSh.** Surface mgnetization measurements on a set-up in which the **polar Kerr** rotation is determined as a function of a perpendicular applied field yield the surface coercivity H_{CS} [6].

'he (magnetic) film thickness h is determined fran the prcduct $M_S \cdot h$ and $M_S = 460 \text{ kA/m}$.

Since sputtering conditions are less homogeneous in magnetron qxtterirq than in the **RF** node, the former smnples were divided into "centre" and "off entre" samples **as** described in **[71.** Series B and D of the "centre" type have a higher $CR = H_{CS}/H_{CY}$ and a higher thickness than series A and C belonging to the "off centre" type.

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All series consists of 7 films.

Fran torque measurements the value of **K1** was found to be **0.9** and 1.9x105J/m for RF and magnetron sputtered films, respectively.

hase of eq. (1) in a CoCr film with a thickness of 1 μ m is ?he precession of the polarization vector to **be** expected on cnly 70, and hence $\cos \phi_m$ > 0.99.

To make the difference of D_{1i} $(i = x,y,z)$ from 1 better cbservable, **we** perforired the **ND** experiments on stacks of *7,* **12** *OT* **14** films rather than on a single film, *so* in fact we **msured** (Dii)N (N = **7, 12,** 14). **Thus** we were able to study films with thicknesses from $4,84$ down to 0.31 μ m. Table 1 gives a review of the films **used** in this **study.**

Table 1 review of CoCr films used.

M_S h	ħ (μm)	Œ	$numb.$ of films	$\bm{\varphi}_{\mathfrak{m}}$
(A)				(degr)
0.144	Q.31	\varnothing .4	14	2.22
0.242	\varnothing .52	\varnothing .3	14	3.7
0.421	Ø.95	Ø.3	14	6.48
0.855	1.90	$\emptyset.4$	12	13.2°
2.22	4.84	ø.7	14	34.2
		RF sputtered films		

B. Magnetron sputtered film

To measure the quantities D_{XX} , D_{YY} and D_{ZZ} as a function **of** @ (Fig. **21, we** rotated the sample steprise and measured in each setting the intensities denoted Ixx, I_{YY} and I_{zz}, respectively. The corresponding matrix elements are calculated Q' Dii (Is - Iii)/IsP (i = x,y,z) with P (= **0.94)** the plarizing per of the set-up and **Is** the intensity of the fully depolarized beam.

Films were measured in the remanent states after applying an **external** field larger than **7** kA/m *(8* Me) either perpendicular *ar* parallel to the **plane** of the film. In the latter case the sample was mounted such that the remanence was perpendicular to the axis of rotation (Fig. 1).

Fig. 2 Behaviour of the diagonal elements in sample 080384 after in-plane saturation as a function of transmission angle.

RESULTS.

(i) DaMin height.

From D_{XX} 1 (Fig. 2) in all experimental results follows that the damin magnetization is perpendicular to the plane of the films **C31.**

The actual precession of the polarization vector is manifest *dy* in % and Dzz and appears to **be less** than the value calculated with *eq.* **(1)** . Therefore **we** intrcduce **the** quantity heff defined **by**

$$
h_{eff}/h = \arccos(\sqrt[M]{D}) / \phi_m \qquad (3)
$$

with D the average of D_{yy} and D_{ZZ} for $\theta = \emptyset$ and N the number of stacked films. The quotient h_{eff}/h is plotted in Fig. 3a and b as a function of h in both magnetic states for RF and magnetron spttered films, respectively.

Fig. 3 Effective height measured in RF (a) and magnetron
films (b) as a function of film thickness after perpendicular (open symbols) and in-plane (black symbols) saturation. In (b) square and circular symbols correspond to films with high and low CR, respectively.

The behaviour of RF and magnetron sputtered films is
qualitatively similar. In the remanent state after qualitatively similar. In the perpendicular saturation heff appears to approach h in thin films. In the in-plane remanent state heff/h also increases upon decreasing film thickness, but tends to remain well below 1. The low CR of the magnetron series A and C is found to correlated with a lower h_{eff} compared with series B and D *bd.th* a CR close to 1 (Fig. **3b,** table **1).**

(ii) Domain section width.

Using the plots of D_{VV} and D_{ZZ} , δ is determined from the angle $\theta_{\rm O}$ (Fig. 2). From eq. (2) we can deduce that

$$
\delta = \frac{2}{2} \quad \theta_{\text{o}} \cdot \text{h} \tag{4}
$$

Setting h equal to heff in eq. (4) yields the behaviour plotted in Figs. 4a and b for δ as a function of thickness in RF and in magnetron sputtered films, respectively. We notice that δ is \sim 1.7 times as large after perpendicular saturation as after in-plane saturation. Moreover, for magnetron films δ is about 1.6 times as large as for RF-films. In the RF film of 0.31 μ m hardly any dependence of D_{yy} and D_{ZZ} on θ was coserved, so we can give no reliable value for δ .

In all plots δ can be described as $\sim h^x$, $with$ for $x = \emptyset.6$ and $\emptyset.8$ (+ $\emptyset.95$) after in-plane and RF films perpendicular saturation, respectively and for magnetron films $x = \emptyset$.7 and \emptyset .8 (+ \emptyset . \emptyset 5) respectively.

Fig. 4 Domain section width δ measured in RF (a) and magnetron films (b) as a function of film thickness. Symbols as in Fig. 3. The broken lines are a best fit to the observations; the full lines correspond to the domain width d according to "reversed spike theory". By the "curvature" of the domains d should be $\sim \frac{\delta}{2}$.

DISCUSSION.

(i) Domain height, heff.

In an earlier [6] and in a parallel [7] study on CoCr films it is reported that the quantity CR in RF films abruptly decreases from 1.3 to 0.5 above a critical film thickness of 125 nm.

The critical thickness for magnetron films was found to be 1.1 and 0.8 μ m for centre and off-centre samples, respectively. The increase in CR is explained by the vanishing of reversed domains or spikes from the surface in films thinner than the critical thickness. An order of magnitude estimate [7] based on theoretical calculations of flux closure in uniaxial systems by "reversed spike domains" i.e. "branching" of the main domains [8,9,10] shows that spike domains in CoCr are expected to disappear at a films thickness near this critical value.

Also the present observation that heff/h after perpendicular saturation approaches l'at a thickness near this value is consistent with spike domain theory. In this theory it is Expression expected that the magnetron series A and C with a
"low" CR ("many spikes") should have a lower heff than the series B and D with a "high" CR value. This is indeed found after perpendicular saturation, as can be seen in Fig. 3b.

(ii) Domain section width δ and domain width d.

A sharp knife cross-section through a serpentine domain structure reveals the section widht distribution. Its average is larger than the shortest perpendicular "cross over" of a domain by a factor of ~2, depending on the "curvature" of the serpentines. We assume that δ is proportional to the domain width d. In continuous domain models with free poles or closure domains, e.g. the Kittel model [11] the dependence of d on h is described with a power $1/2$: $d = \emptyset .19 h^{1/2}$ and $\emptyset .21 h^{1/2}$ in RF and magnetron films respectively. In spike domain theory one finds $d = \emptyset$.11 h2/3 and \emptyset .10 h2/3, respectively (d and h in μ m). The present observations that the exponent of h has values between 0.6 and 0.8 is in favor of the spike domain model and in agreement with measurements by Gemperle and coworkers [12] on Co platelets.

The Kittel model predicts a weak dependence of d on K1. However, we observe that δ in magnetron films is 1.6 times as much as in RF films, whereas K1 differs by a factor of 2.

this model does also not describe the observed K1 S_{Ω} dependence of δ . It is concluded from this and other observations that RF and magnetron films differ in more respects (e.g. internal stress and coercivity [7]) than merily the quantity K1.

The difference of heff and δ after perpendicular and after in-plane saturation, found in all our films is probably correlated with domain nucleation, which proceeds in different ways after both saturated states. It proves that the columnar morphology is not the only factor defining the domain structure, but that also the magnetic history is important.

CONCLUSION.

We have studied the effective height and the domain section width in sputtered CoCr films. In the same film both quantities are different after in-plane or after perpendicular saturation. The increase of heff with decreasing film thickness is explained by the vanishing of "reversed spike domains" below a critical thickness. These phenomena and the 2/3 power dependence of the domain width on film thickness are more consistent with the spike model than with the Kittel model for a continuous medium. The lower heff found in magnetron films with a lower surface/bulk coercivity ratio is also consistent with spike domain theory.

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